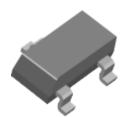
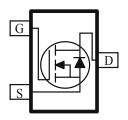
## N-Channel 30V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low  $r_{DS(on)}$  and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

PRODUCT SUMMARY				
<b>V</b> <sub>DS</sub> (V)	$\mathbf{r}_{\mathrm{DS}}(\mathbf{V}) \qquad \mathbf{r}_{\mathrm{DS}(\mathrm{on})}(\mathbf{\Omega}) \qquad \mathbf{I}_{\mathrm{D}}(\mathbf{A})$			
30	$0.058 @V_{CS} = 10 V$	2.0		
	$0.082 @V_{CS} = 4.5V$	1.7		

- Low r<sub>DS(on)</sub> provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe SC70-3 saves board space
- Fast switching speed
- High performance trench technology





ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C UNLESS OTHERWISE NOTED)						
Parameter			Maximum	Units		
Drain-Source Voltage		V <sub>DS</sub>	30	V		
Gate-Source Voltage	urce Voltage			v		
Continuous Drain Current <sup>a</sup>	$T_A=25^{\circ}C$	I.	2.0	А		
	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	цD	1.7			
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	±20			
Continuous Source Current (Diode Conduction) <sup>a</sup>		Is	1.6	Α		
	$T_A=25^{\circ}C$	D	0.34	W		
Power Dissipation <sup>a</sup>	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	тD	0.22	• •		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Maximum	Units			
	t <= 5 sec	D	100	<sup>0</sup> 0/11/		
Maximum Junction-to-Ambient <sup>a</sup>	Steady-State	$R_{THJA}$	166	°C/W		

Notes

a. Surface Mounted on 1" x 1" FR4 Board.

b. Pulse width limited by maximum junction temperature

SPECIFICATIONS (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED)								
Parameter	Symbol	Test Conditions	Limits			Unit		
i urumeter	Symbol	Test conutions	Min	Тур	Max	om		
Static					-			
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \text{ uA}$	1			V		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			±100	nA		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 24 V, V_{GS} = 0 V$	0 V		1	uA		
Zero Gate Voltage Drain Current	IDSS	$V_{DS} = 24 V, V_{GS} = 0 V, T_J = 55^{\circ}C$			10	uA		
On-State Drain Current <sup>A</sup>	I <sub>D(on)</sub>	$V_{DS} = 5 V, V_{GS} = 10 V$	10			Α		
Drain-Source On-Resistance <sup>A</sup>	ľ.	$V_{GS} = 10 \text{ V}, I_D = 2.0 \text{ A}$			58	mΩ		
	r <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, I_D = 1.7 \text{ A}$			82	1115.2		
Forward Tranconductance <sup>A</sup>	$g_{\rm fs}$	$V_{DS} = 10 \text{ V}, I_D = 2.0 \text{ A}$		11.3		S		
Diode Forward Voltage	V <sub>SD</sub>	$I_{\rm S} = 1.6$ A, $V_{\rm GS} = 0$ V		0.75		V		
Dynamic <sup>b</sup>								
Total Gate Charge	Qg			7.5				
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = 10 V, V_{GS} = 5 V, I_D = 2.0 A$		0.6		nC		
Gate-Drain Charge	Q <sub>gd</sub>			1.0				
Turn-On Delay Time	t <sub>d(on)</sub>			8				
Rise Time	t <sub>r</sub>	$V_{DD} = 10 \text{ V},  R_L = 15 \Omega,  I_D = 1 \text{ A},$		24		nc		
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GEN} = 4.5 V$		35		ns		
Fall-Time	t <sub>f</sub>			10		1		

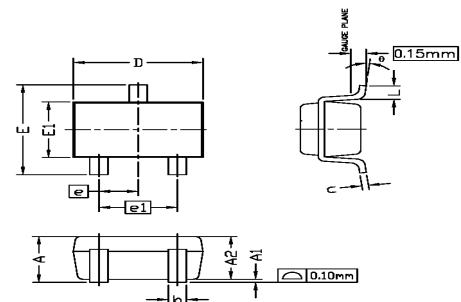
Notes

- a. Pulse test:  $PW \le 300$ us duty cycle  $\le 2\%$ .
- b. Guaranteed by design, not subject to production testing.

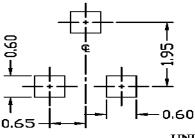
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## Package Information

SC70 PACKAGE OUTLINE



RECOMMENDED LAND PATTERN



SYMBOLS	DIMENS	IONS IN MILLIMBTERS		DIMENSIONS IN INCHES		
a 1 MISOLS	MIN	NOM	MAX	MIN	NOM	MAX
Α			1.10			0.043
A1	0.00		0.10	0.00		0.004
A2	0.7	0.9	1.00	0.028	0.035	0.039
ь	0.15		0.30	0.006		0.012
c	0.08		0.22	0.003		0.009
D	1.85	2,10	2,15	0.073	0.083	0.085
Е	1.80	2.30	2.40	0.071	0.091	0.094
e	0.65 BSC			0.026 BSC		
el		1.30 BSC	SC 0.051 BSC			
<b>E</b> 1	1.1	1.30	1.4	0.043	0.051	0.055
L	0.26	0.36	0.46	0.010	0.014	0.018
Ð	0°	4°	8°	0°	4°	8°

UNIT: mm

## NOTE

- 1. ALL DIMENSIONS ARE IN MILLMETERS.
- 2. DIMENSIONS ARE INCLUSIVE OF PLATING.
- 3. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
- MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 3 MILS EACH.
- 4. DIE IS FACING UP FOR MOLD AND FACING DOWN FOR TRIM/FORM. ie:REVERSE TRIM/FORM.
- 5. DIMENSION L IS MEASURED IN GAUGE PLANE.
- 6. CONTROLLING DIMENSION IS MILLIMETER. CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.